



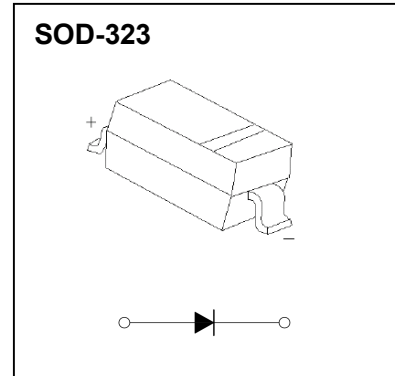
SOD-323 Plastic-Encapsulate Diodes

SD101AWS SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Very Low Reverse Capacitance

MARKING: S1



MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _R RM	Repetitive Peak Reverse Voltage	60	V
V _R WM	Working Peak Reverse Voltage		
V _R	DC Blocking Voltage		
V _{R(RMS)}	RMS reverse voltage	42	V
I _{FM}	Forward Continuous Current	15	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @ t ≤ 1s	50	mA
	@t=10μs	2	A
P _D	Power Dissipation	200	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	500	°C/W
T _j	Junction Temperature	125	°C
T _{stg}	Storage Temperature	-50~+150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V _(BR)	I _R =10μA	60			V
Reverse current	I _R	V _R =50V			0.2	μA
Forward voltage	V _F	I _F =1mA			0.41	V
		I _F =15mA			1	
Total capacitance	C _{tot}	V _R =0V, f=1MHz			2	pF
Reverse recovery time	t _{rr}	I _F = I _R =5mA, I _{rr} =0.1×I _R , R _L =100Ω			1	ns